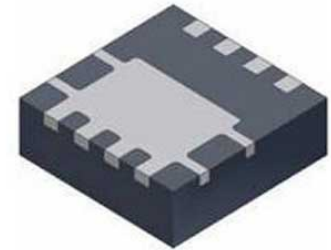


MOSFET, N CHANNEL, 30V, 0.0096OHM, 16.5A, Transistor Polarity:N Channel, Continuous Drain Current Id:16.5A, Drain Source Voltage Vds:30V, On Resistance Rds(on):0.0096ohm, Rds(on) Test Voltage Vgs:10V, Power Dissipation Pd:31W

Manufacturers	<a href="#">ON Semiconductor, LLC</a>
Package/Case	Power 33
Product Type	Transistors
RoHS	Green
Lifecycle	



Images are for reference only

Please submit RFQ for FDMC8878 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

## General Description

This N-Channel MOSFET is a rugged gate version of an advanced Power Trench process. It has been optimized for power management applications.

## Features

Low Profile—1mm max in MLP 3.3X3.3

## Application

ONSEMI

## Related Products



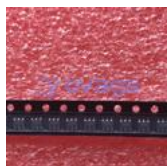
### [FDC645N](#)

ON Semiconductor, LLC  
SSOT-6



### [FDC637BNZ](#)

ON Semiconductor, LLC  
SSOT-6



### [FDC6305N](#)

ON Semiconductor, LLC  
SSOT-6



### [FDC602P](#)

ON Semiconductor, LLC  
SOT163



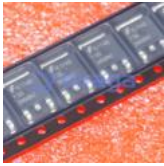
[FDD8647L](#)

ON Semiconductor, LLC  
TO-252-3



[FDB070AN06A0](#)

ON Semiconductor, LLC  
TO-263



[FDD5N50NZTM](#)

ON Semiconductor, LLC  
TO-252



[FDD3670](#)

ON Semiconductor, LLC  
TO-252AA